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November 2013

FDB12N50TM

N-Channel UniFETTM MOSFET

500 V, 11.5 A, 650 mΩ

Features

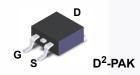
- $R_{DS(on)} = 550 \text{ m}\Omega \text{ (Typ.)} @ V_{GS} = 10 \text{ V, } I_D = 6 \text{ A}$
- Low Gate Charge (Typ. 22 nC)
- Low Crss (Typ. 12 pF)
- 100% Avalanche Tested
- · RoHS Compliant

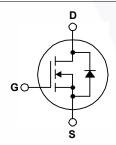
Applications

- Lighting
- Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDB12N50TM	Unit
V _{DSS}	Drain to Source Voltage			500	V
V _{GSS}	Gate to Source Voltage			±30	V
	Drain Current	- Continuous (T _C = 25°C)		11.5	Α
ID	Diain Current	- Continuous (T _C = 100°C)		6.9	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	46	Α
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	456	mJ
I _{AR}	Avalanche Current		(Note 1)	11.5	Α
E _{AR}	Repetitive Avalanche Ene	ergy	(Note 1)	16.7	mJ
dv/dt	Peak Diode Recovery dv	/dt	(Note 3)	4.5	V/ns
n	Dower Discinction	$(T_C = 25^{\circ}C)$		165	W
P_{D}	Power Dissipation	- Derate above 25°C		1.33	W/°C
T _J , T _{STG}	Operating and Storage To	emperature Range		-55 to +150	°C
T _L	Maximum Lead Tempera 1/8" from Case for 5 Sec	ture for Soldering Purpose, onds		300	°C

Thermal Characteristics

Symbol	Parameter	FDB12N50TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.75	
В	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (1 in ² pad of 2 oz copper), Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB12N50	FDB12N50TM	D ² -PAK	330mm	24mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A$, $V_{GS} = 0V$, $T_J = 25^{\circ}C$	500	-	-	V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.66	-	V/°C
1	Zoro Cata Valtago Drain Current	V _{DS} = 500V, V _{GS} = 0V	-	-	1	
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 400V, T_C = 125^{\circ}C$	-	-	10	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10V, I _D = 6A	-	0.55	0.65	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 25V, I_{D} = 6A$	-	11	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V f = 1MHz		985	1315	pF
C _{oss}	Output Capacitance			140	190	pF
C _{rss}	Reverse Transfer Capacitance	1 - 111112	-\	12	17	pF
Q_g	Total Gate Charge at 10V		- \	22	30	nC
Q _{gs}	Gate to Source Gate Charge	$V_{DS} = 400V, I_{D} = 11.5A$	-	6	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	$V_{GS} = 10V$ (Note 4)	-	10	1	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time			-	25	60	ns
t _r	Turn-On Rise Time	V _{DD} = 250V, I _D = 11.5A		-	60	130	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 25\Omega$		-	45	105	ns
t _f	Turn-Off Fall Time		(Note 4)	-	35	85	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Dioc	Maximum Continuous Drain to Source Diode Forward Current		-	11.5	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	46	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 11.5A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 11.5A	-	370	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	3.8	_	μС

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 6.9mH, I $_{AS}$ = 11.5A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C
- 3. I $_{SD} \leq$ 11.5A, di/dt \leq 200A/ $\mu s,~V_{DD} \leq$ BV $_{DSS},~Starting~T_{J}$ = 25°C
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics

Figure 1. On-Region Characteristics

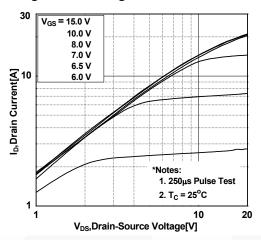


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

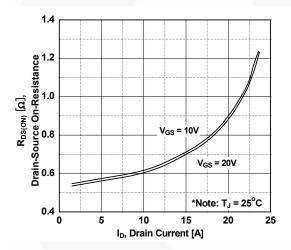


Figure 5. Capacitance Characteristics

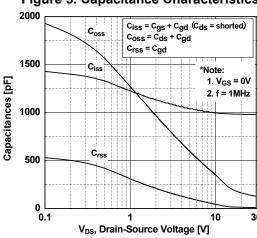


Figure 2. Transfer Characteristics

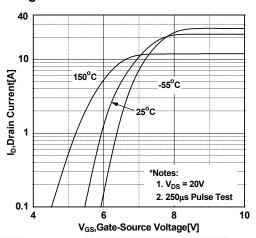


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

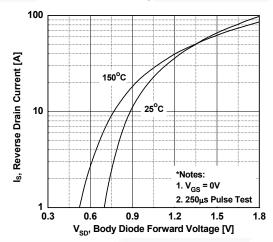
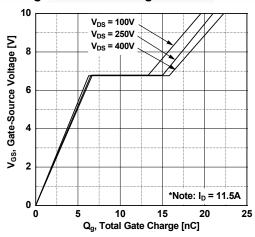


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

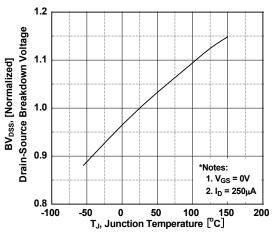


Figure 9. Maximum Safe Operating Area



Figure 8. On-Resistance Variation vs. Temperature

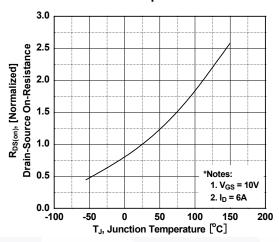
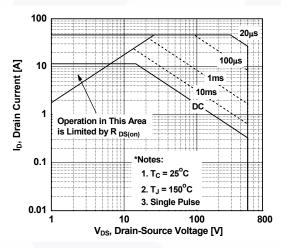


Figure 10. Maximum Drain Current vs. Case Temperature



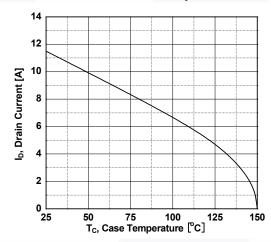


Figure 11. Transient Thermal Response Curve

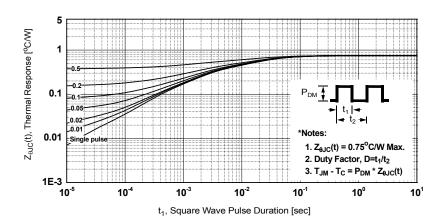


Figure 12. Gate Charge Test Circuit & Waveform

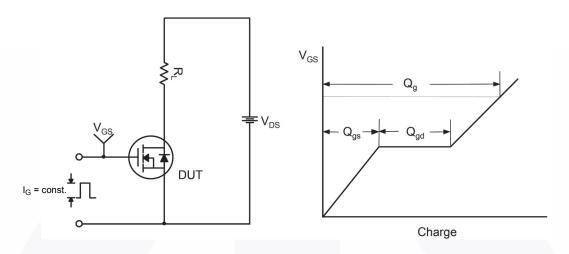


Figure 13. Resistive Switching Test Circuit & Waveforms

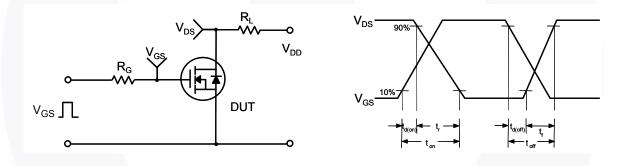
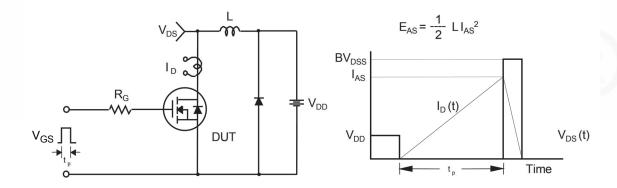


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



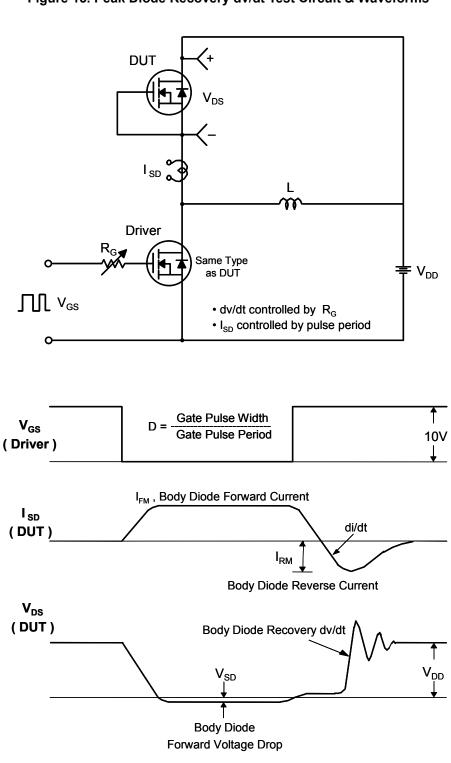


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

TO-263 2L (D²PAK)

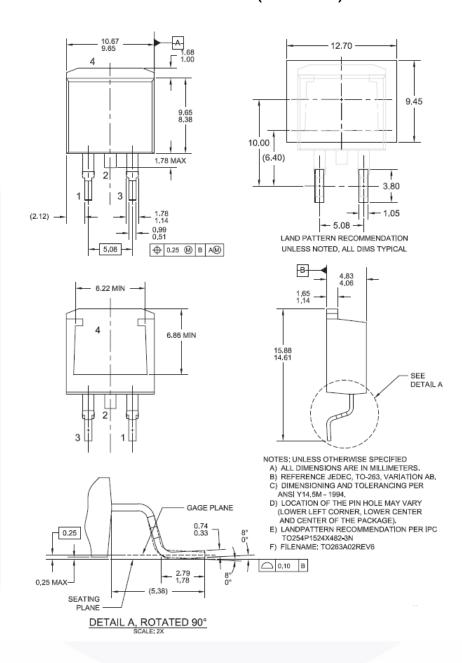


Figure 16. 2LD, TO263, Surface Mount

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Dimension in Millimeters





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